

## IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (Original): A semiconductor substrate comprising:  
first and second surfaces; and  
an oxide film apart from said first and second surfaces and extending throughout said semiconductor substrate.

Claim 2 (Original): The semiconductor substrate according to claim 1 wherein the distance between said oxide film and said second surface corresponds to a thickness on the order of  $10^{-3}$  of a thickness of said semiconductor substrate.

Claim 3 (Original): The semiconductor substrate according to claim 1 wherein said oxide film has a thickness of 400 to 1000 nm.

Claim 4 (Original): The semiconductor substrate according to claim 2 wherein said oxide film has a thickness of 400 to 1000 nm.

Claim 5 (Original): The semiconductor substrate according to claim 1 further comprising an epitaxial layer disposed on said first surface.

Claim 6 (Original): The semiconductor substrate according to claim 2 further comprising an epitaxial layer disposed on said first surface.

Claim 7 (Original): The semiconductor substrate according to claim 3 further comprising an epitaxial layer disposed on said first surface.

Claim 8 (Original): The semiconductor substrate according to claim 4 further comprising an epitaxial layer disposed on said first surface.

Claim 9 (Original): A semiconductor device comprising:  
a semiconductor substrate having first and second surfaces;

an oxide film apart from said first and second surfaces, and extending throughout said semiconductor substrate;

an epitaxial layer disposed on said first surface; and

a semiconductor element disposed in said epitaxial layer.

Claim 10 (Original): The semiconductor device according to claim 9 wherein the distance between said oxide film and said second surface corresponds to a thickness on the order of  $10^{-3}$  of a thickness of said semiconductor substrate.

Claim 11 (Original): The semiconductor device according to claim 9 wherein said oxide film has a thickness of 400 to 1000 nm.

Claim 12 (Original): The semiconductor device according to claim 10 wherein said oxide film has a thickness of 400 to 1000 nm.

Claims 13-16 (Canceled).

### DISCUSSION OF THE AMENDMENT

Claims 13-16 have been canceled, leaving original Claims 1-12 for examination.